## 1. General description

PNP low  $V_{CEsat}$  transistor and NPN Resistor-Equipped Transistor (RET) in a SOT457 (SC-74) small Surface Mounted Device (SMD) plastic package.

## 2. Features and benefits

- Low V<sub>CEsat</sub> transistor and resistor-equipped transistor in one package
- Low threshold voltage (< 1 V) compared to MOSFET</li>
- · Low drive power required
- Space-saving solution
- Reduction of component count
- · Qualified according to AEC-Q101 and recommended for use in automotive applications

## 3. Applications

- · Supply line switches
- · Battery charger switches
- · High-side switches for LEDs, drivers and backlights
- · Portable equipment

## 4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
TR1; PNP low	V <sub>CEsat</sub> transistor						
V <sub>CEO</sub>	collector-emitter voltage	open base		-	-	-60	V
I <sub>C</sub>	collector current		[1]	-	-	-1	Α
R <sub>CEsat</sub>	collector-emitter saturation resistance	$I_C$ = -1 A; $I_B$ = -100 mA; $T_{amb}$ = 25 °C; pulsed; $t_p \le 300$ μs; $\delta_{factor} \le 0.02$		-	255	340	mΩ
TR2; NPN resis	stor-equipped transistor	•					_
V <sub>CEO</sub>	collector-emitter voltage	open base		-	-	50	V
Io	output current			-	-	100	mA
R1	bias resistor 1 (input)			7	10	13	kΩ
R2/R1	bias resistor ratio			0.8	1	1.2	

<sup>[1]</sup> Device mounted on a ceramic Printed-Circuit Board (PCB), Al<sub>2</sub>O<sub>3</sub>, standard footprint.



60 V, 1 A PNP loadswitch double transistor

# 5. Pinning information

**Table 2. Pinning information** 

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	E1	emitter TR1		C1 I2 GND2
2	B1	base TR1		
3	O2	output (collector) TR2	<u> </u>	R1 R2
4	GND2	GND (emitter) TR2		TR2
5	12	input (base) TR2	<u> </u>	TR1
6	C1	collector TR1	TSOP6 (SOT457)	<del></del>
				E1 B1 O2 sym036

# 6. Ordering information

**Table 3. Ordering information** 

Type number	Package				
	Name	Description	Version		
PBLS6003D-Q	TSOP6	plastic, surface-mounted package (SC-74; TSOP6); 6 leads	SOT457		

## 7. Marking

## Table 4. Marking codes

Type number	Marking code
PBLS6003D-Q	F3

## 60 V, 1 A PNP loadswitch double transistor

# 8. Limiting values

#### Table 5. Limiting values

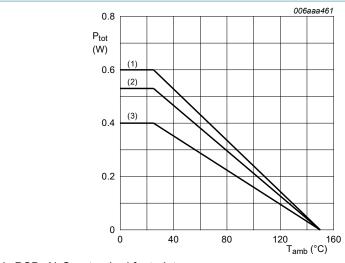
In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
TR1; PNP lo	w V <sub>CEsat</sub> transistor				_	
V <sub>CBO</sub>	collector-base voltage	open emitter		-	-80	V
V <sub>CEO</sub>	collector-emitter voltage	open base		-	-60	V
V <sub>EBO</sub>	emitter-base voltage	open collector		-	-5	V
I <sub>C</sub>	collector current		[1]	-	-700	mA
			[2]	-	-850	mA
Ісм			[3]	-	-1	А
I <sub>CM</sub>	peak collector current	single pulse; t <sub>p</sub> ≤ 1 ms		-	-2	А
I <sub>B</sub>	base current			-	-300	mA
I <sub>BM</sub>	peak base current	single pulse; t <sub>p</sub> ≤ 1 ms		-	-1	А
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> ≤ 25 °C	[1]	-	250	mW
			[2]	-	350	mW
			[3]	-	400	mW
TR2; NPN re	esistor-equipped transistor					
$V_{CBO}$	collector-base voltage	open emitter		-	50	V
$V_{CEO}$	collector-emitter voltage	open base		-	50	V
$V_{EBO}$	emitter-base voltage	open collector		-	10	V
$V_{I}$	input voltage			-10	40	V
I <sub>O</sub>	output current			-	100	mA
I <sub>CM</sub>	peak collector current			-	100	mA
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> ≤ 25 °C	[1]	-	200	mW
			[2]	-	200	mW
			[3]	-	200	mW
Per device						
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> ≤ 25 °C	[1]	-	400	mW
			[2]	-	530	mW
			[3]	-	600	mW
Tj	junction temperature			-	150	°C
T <sub>amb</sub>	ambient temperature			-65	150	°C
T <sub>stg</sub>	storage temperature			-65	150	°C

<sup>[1]</sup> Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 1 cm $^2$ . Device mounted on a ceramic PCB, Al<sub>2</sub>O<sub>3</sub>, standard footprint.

#### 60 V, 1 A PNP loadswitch double transistor



- (1) Ceramic PCB, Al<sub>2</sub>O<sub>3</sub>, standard footprint (2) FR4 PCB, mounting pad for collector 1 cm<sup>2</sup>
- (3) FR4 PCB, standard footprint

**Power derating curves** Fig. 1.

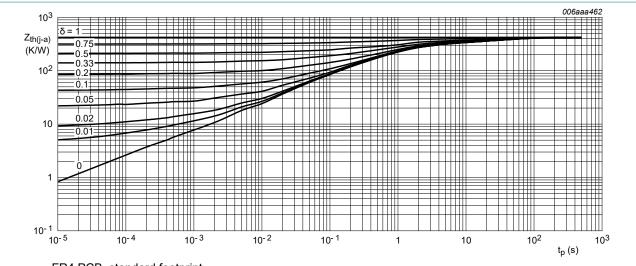
## 9. Thermal characteristics

**Table 6. Thermal characteristics** 

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Per device				'			'
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	[1]	-	-	312	K/W
			[2]	-	-	236	K/W
			[3]	-	-	208	K/W
TR1; PNP low	V <sub>CEsat</sub> transistor		,	'	'		'
$R_{th(j-sp)}$	thermal resistance from junction to solder point			-	-	105	K/W

- Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 1 cm<sup>2</sup>.
- Device mounted on a ceramic PCB, Al<sub>2</sub>O<sub>3</sub>, standard footprint. [3]

#### 60 V, 1 A PNP loadswitch double transistor



FR4 PCB, standard footprint

Fig. 2. TR1 (PNP): Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

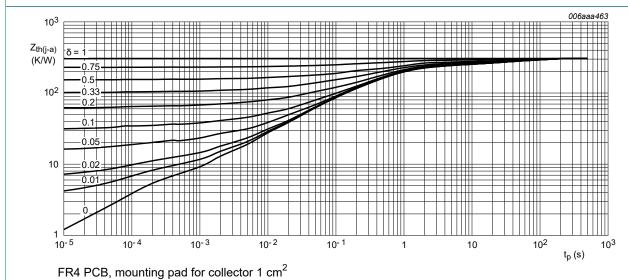


Fig. 3. TR1 (PNP): Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

### 60 V, 1 A PNP loadswitch double transistor

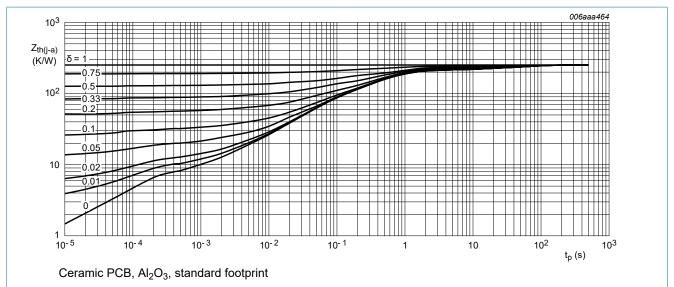


Fig. 4. TR1 (PNP): Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

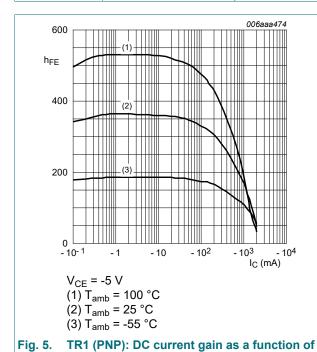
## 10. Characteristics

**Table 7. Characteristics** 

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
TR1; PNP Io	ow V <sub>CEsat</sub> transistor				'	'
I <sub>CBO</sub>	collector-base cut-off	$V_{CB} = -60 \text{ V}; I_{E} = 0 \text{ A}; T_{amb} = 25 ^{\circ}\text{C}$	-	-	-100	nA
	current	V <sub>CB</sub> = -60 V; I <sub>E</sub> = 0 A; T <sub>j</sub> = 150 °C	-	-	-50	μA
I <sub>CES</sub>	collector-emitter cut-off current	V <sub>CE</sub> = -60 V; V <sub>BE</sub> = 0 V; T <sub>amb</sub> = 25 °C	-	-	-100	nA
I <sub>EBO</sub>	emitter-base cut-off current	V <sub>EB</sub> = -5 V; I <sub>C</sub> = 0 A; T <sub>amb</sub> = 25 °C	-	-	-100	nA
h <sub>FE</sub>	DC current gain	$V_{CE}$ = -5 V; $I_{C}$ = -1 mA; $T_{amb}$ = 25 °C	200	350	-	
		$V_{CE}$ = -5 V; $I_{C}$ = -500 mA; pulsed; $t_{p}$ ≤ 300 μs; δ ≤ 0.02; $T_{amb}$ = 25 °C	150	230	-	
		$V_{CE}$ = -5 V; $I_{C}$ = -1 A; pulsed; $t_{p}$ ≤ 300 μs; $\delta$ ≤ 0.02; TR1; PNP low $V_{CEsat}$ transistor; $T_{amb}$ = 25 °C	100	160	-	
V <sub>CEsat</sub> collector-emitte	collector-emitter	$I_C$ = -100 mA; $I_B$ = -1 mA; $T_{amb}$ = 25 °C	-	-110	-175	mV
	saturation voltage	$I_C$ = -500 mA; $I_B$ = -50 mA; pulsed; $t_p \le$ 300 μs; δ ≤ 0.02; $T_{amb}$ = 25 °C	-	-135	-180	mV
		$I_C$ = -1 A; $I_B$ = -100 mA; pulsed; $t_p \le$ 300 μs; δ ≤ 0.02; $T_{amb}$ = 25 °C	-	-255	-340	mV
R <sub>CEsat</sub>	collector-emitter saturation resistance	$I_C$ = -1 A; $I_B$ = -100 mA; $T_{amb}$ = 25 °C; pulsed; $t_p \le 300$ μs; $\delta_{factor} \le 0.02$	-	255	340	mΩ
V <sub>BEsat</sub>	base-emitter saturation voltage	$I_C$ = -1 A; $I_B$ = -50 mA; $T_{amb}$ = 25 °C; pulsed; $t_p \le 300$ μs; $\delta_{factor} \le 0.02$	-	-0.95	-1.1	V
$V_{BEon}$	base-emitter turn-on voltage	$V_{CE}$ = -5 V; $I_{C}$ = -1 A; $T_{amb}$ = 25 °C; pulsed; $t_{p}$ ≤ 300 μs; $\delta_{factor}$ ≤ 0.02	-	-0.82	-0.9	V

### 60 V, 1 A PNP loadswitch double transistor

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
t <sub>d</sub>	delay time	I <sub>C</sub> = -0.5 A;	-	11	-	ns
t <sub>r</sub>	rise time	I <sub>Bon</sub>	-	30	-	ns
t <sub>on</sub>	turn-on time	T <sub>amb</sub> = 25 °C	-	41	-	ns
t <sub>s</sub>	storage time		-	205	-	ns
t <sub>f</sub>	fall time		-	55	-	ns
t <sub>off</sub>	turn-off time		-	260	-	ns
C <sub>c</sub>	collector capacitance	V <sub>CB</sub> = -10 V; I <sub>E</sub> = 0 A; i <sub>e</sub> = 0 A; f = 1 MHz; T <sub>amb</sub> = 25 °C	-	9	15	pF
f <sub>T</sub>	transition frequency	$V_{CE}$ = -10 V; $I_{C}$ = -50 mA; f = 100 MHz; $T_{amb}$ = 25 °C	150	185	-	MHz
TR2; NPN re	esistor-equipped transisto	r				
I <sub>CBO</sub>	collector-base cut-off current	$V_{CB} = 50 \text{ V}; I_{E} = 0 \text{ A}; T_{amb} = 25 \text{ °C}$	-	-	100	nA
I <sub>CEO</sub>	collector-emitter cut-off	V <sub>CE</sub> = 30 V; I <sub>B</sub> = 0 A; T <sub>amb</sub> = 25 °C	-	-	1	μΑ
	current	V <sub>CE</sub> = 30 V; I <sub>B</sub> = 0 A; T <sub>j</sub> = 150 °C	-	-	50	μA
I <sub>EBO</sub>	emitter-base cut-off current	$V_{EB} = 5 \text{ V}; I_{C} = 0 \text{ A}; T_{amb} = 25 \text{ °C}$	-	-	400	μA
h <sub>FE</sub>	DC current gain	V <sub>CE</sub> = 5 V; I <sub>C</sub> = 5 mA; T <sub>amb</sub> = 25 °C	30	-	-	
V <sub>CEsat</sub>	collector-emitter saturation voltage	$I_C = 10 \text{ mA}; I_B = 0.5 \text{ mA}; T_{amb} = 25 \text{ °C}$	-	-	150	mV
V <sub>I(off)</sub>	off-state input voltage	V <sub>CE</sub> = 5 V; I <sub>C</sub> = 100 μA; T <sub>amb</sub> = 25 °C	-	1.1	8.0	V
V <sub>I(on)</sub>	on-state input voltage	V <sub>CE</sub> = 0.3 V; I <sub>C</sub> = 10 mA; T <sub>amb</sub> = 25 °C	2.5	1.8	-	V
R1	bias resistor 1 (input)		7	10	13	kΩ
R2/R1	bias resistor ratio		0.8	1	1.2	
C <sub>c</sub>	collector capacitance	$V_{CB}$ = 10 V; $I_{E}$ = 0 A; $i_{e}$ = 0 A; f = 1 MHz; $T_{amb}$ = 25 °C	-	-	2.5	pF



collector current; typical values

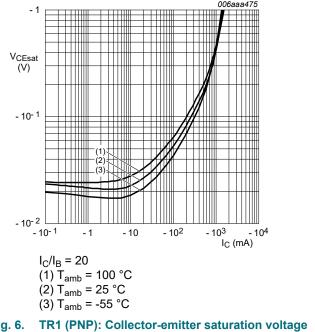


Fig. 6. TR1 (PNP): Collector-emitter saturation voltage as a function of collector current; typical values

#### 60 V, 1 A PNP loadswitch double transistor

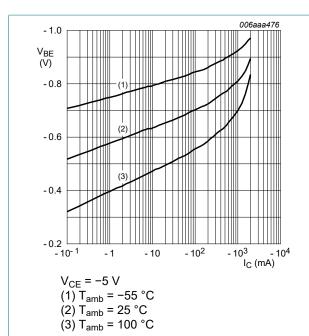


Fig. 7. TR1 (PNP): Base-emitter voltage as a function of collector current; typical values

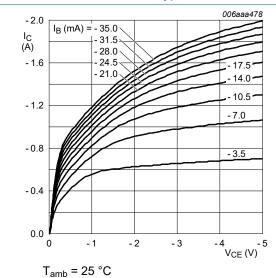
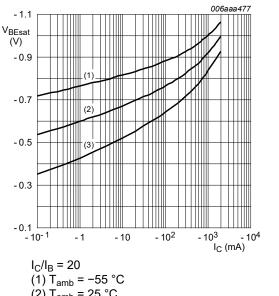
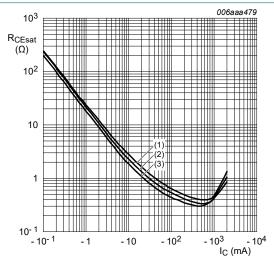


Fig. 9. TR1 (PNP): Collector current as a function of collector-emitter voltage; typical values



 $(1) T_{amb} = -55 °C$ (2)  $T_{amb} = 25 °C$ (3)  $T_{amb} = 100 \, ^{\circ}C$ 

Fig. 8. TR1 (PNP): Base-emitter saturation voltage as a function of collector current; typical values



 $I_{\rm C}/I_{\rm B}=20$ (1)  $T_{amb}$  = 100 °C (2)  $T_{amb} = 25 \, ^{\circ}C$ (3)  $T_{amb} = -55 \, ^{\circ}C$ 

Fig. 10. TR1 (PNP): Collector-emitter saturation resistance as a function of collector current; typical values

### 60 V, 1 A PNP loadswitch double transistor

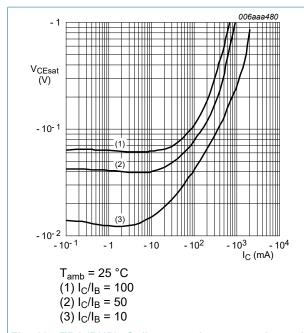
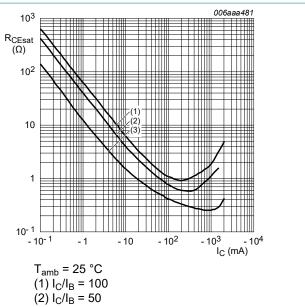
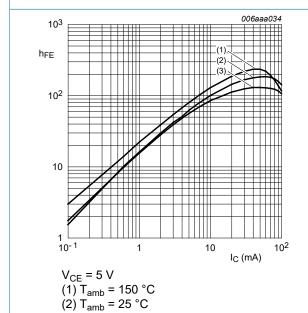


Fig. 11. TR1 (PNP): Collector-emitter saturation voltage as a function of collector current; typical values

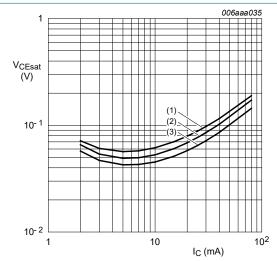


(2)  $I_C/I_B = 50$ (3)  $I_C/I_B = 10$ 

Fig. 12. TR1 (PNP): Collector-emitter saturation resistance as a function of collector current; typical values



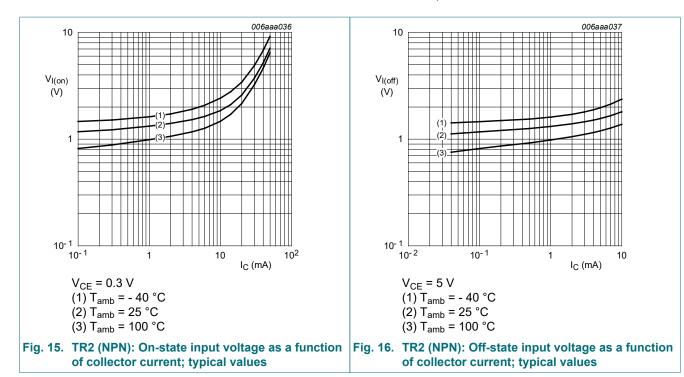
(3)  $T_{amb} = -40 \, ^{\circ}C$ Fig. 13. TR2 (NPN): DC current gain as a function of collector current; typical values



 $I_C/I_B = 20$ (1) T<sub>amb</sub> = 100 °C (2)  $T_{amb} = 25 \, ^{\circ}C$ (3)  $T_{amb} = -40 \, ^{\circ}C$ 

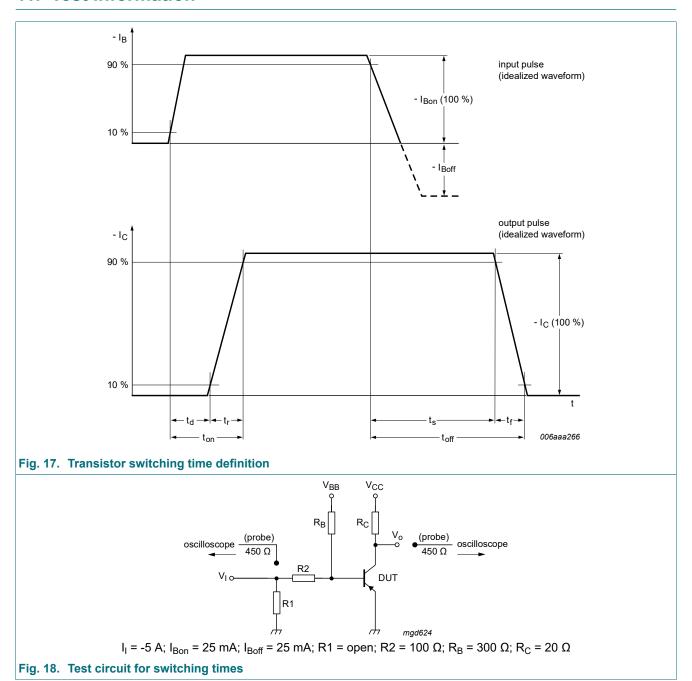
Fig. 14. TR2 (NPN): Collector-emitter saturation voltage as a function of collector current; typical values

### 60 V, 1 A PNP loadswitch double transistor



#### 60 V, 1 A PNP loadswitch double transistor

## 11. Test information

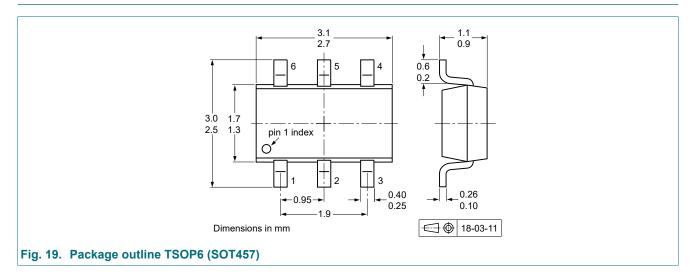


#### **Quality information**

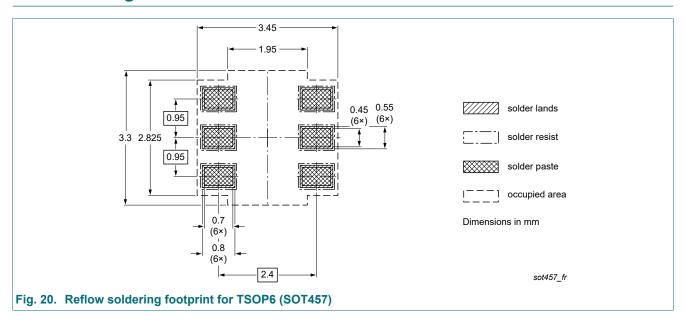
This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101 - Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

## 60 V, 1 A PNP loadswitch double transistor

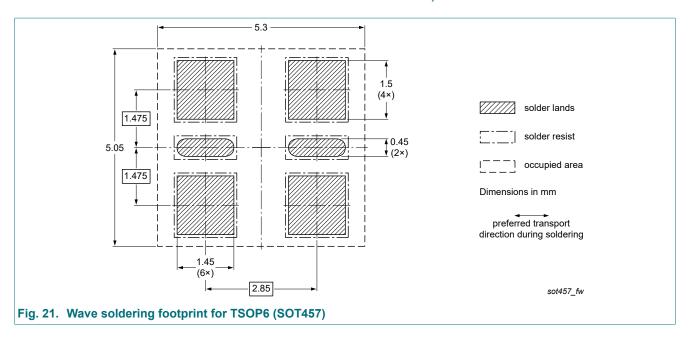
# 12. Package outline



## 13. Soldering



## 60 V, 1 A PNP loadswitch double transistor



## 60 V, 1 A PNP loadswitch double transistor

# 14. Revision history

## Table 8. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
PBLS6003D-Q v.1	20230830	Product data sheet	-	-

## 60 V, 1 A PNP loadswitch double transistor

## 15. Legal information

#### Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- Please consult the most recently issued document before initiating or completing a design.
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## 60 V, 1 A PNP loadswitch double transistor

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For more information, please visit: http://www.nexperia.com For sales office addresses, please send an email to: salesaddresses@nexperia.com Date of release: 30 August 2023

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